Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	172415	FET or (field near effect near transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 15:51
L2	92432	(gate near oxide) or (gate near dielectric) or (gate near insulating near film)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 15:52
L3	29420	l2 same thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 15:52
L4	4381	l3 and (gate near length)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 15:53
L5	82	l4 and (rapid near thermal near oxidation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/15 15:57